

REMARKS

Claims 3, 4 and 7 have been amended to avoid the multiple dependent claim surcharge. Claims 21-26 presented herein correspond to the dependencies eliminated from the amended claims.

The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 any fees that may be required by this paper and to credit any overpayment to that Account.

Respectfully submitted,

MWS:jab

Miles & Stockbridge P.C.
1751 Pinnacle Drive
Suite 500
McLean, Virginia 22102-3833
(703) 610-8652

December 5, 2001

By:

Mitchell W. Shapiro
Mitchell W. Shapiro
Reg. No. 31,568

Shapiro

MARKED-UP VERSION OF THE CLAIMS:

1 3. (Amended) A semiconductor device according to Claim 1
2 [or Claim 2], wherein a power supply voltage applied to the
3 first MOS transistors constituting the input circuit or the
4 output circuit is equal to a power supply voltage applied to
5 the second MOS transistors constituting the internal circuit.

1 4. (Amended) A semiconductor device according to Claim 2
2 [or Claim 3], wherein a gate length of the first MOS
3 transistors is equal to a gate length of the second MOS
4 transistors.

1 7. (Amended) A semiconductor device according to Claim 1
2 [or Claim 2], wherein a power supply voltage applied to the
3 first MOS transistors constituting the input circuit or the
4 output circuit is higher than a power supply voltage applied
5 to the second MOS transistors constituting the internal
6 circuit.